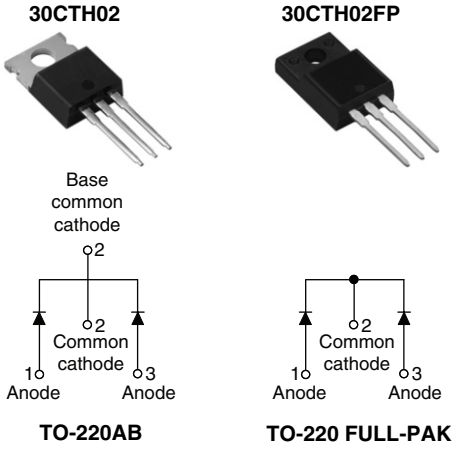
Hyperfast Rectifier, 2 x 15 A FRED Pt™



FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- TO-220 designed and qualified for AEC Q101 level
- TO-220FP designed and qualified for industrial level

DESCRIPTION/APPLICATIONS

200 V series are the state of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, dc-to-dc converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

PRODUCT SUMMARY	
t_{rr} (maximum)	30 ns
$I_{F(AV)}$	2 x 15 A
V_R	200 V

ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage		V_{RRM}		200	V
Average rectified forward current	per diode	$I_{F(AV)}$	T_C = 159 °C	15	A
	(FULL-PAK) per diode		T_C = 125 °C		
	per device			30	
Non-repetitive peak surge current		I_{FSM}	T_J = 25 °C	200	
Operating junction and storage temperatures		T_J, T_{Stg}		- 65 to 175	°C

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_R	I_R = 100 µA	200	-	-	V
Forward voltage	V_F	I_F = 15 A	-	0.92	1.05	
		I_F = 15 A, T_J = 125 °C	-	0.78	0.85	
Reverse leakage current	I_R	V_R = V_R rated	-	-	10	µA
		T_J = 125 °C, V_R = V_R rated	-	5	300	
Junction capacitance	C_T	V_R = 200 V	-	57	-	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body	-	8	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T_C = 25 °C unless otherwise specified)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNITS**
Reverse recovery time	t_{rr}	I_F = 1 A, dI_F/dt = 50 A/µs, V_R = 30 V		-	-	35	ns
		I_F = 1 A, dI_F/dt = 100 A/µs, V_R = 30 V		-	-	30	
		T_J = 25 °C	I_F = 15 A dI_F/dt = 200 A/µs V_R = 160 V	-	26	-	
		T_J = 125 °C		-	40	-	
Peak recovery current	I_{RRM}	T_J = 25 °C		-	2.8	-	A
		T_J = 125 °C		-	6.0	-	
Reverse recovery charge	Q_{rr}	T_J = 25 °C		-	37	-	nC
		T_J = 125 °C		-	120	-	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Maximum junction and storage temperature range		T_J, T_{Stg}		- 65	-	175	°C
Thermal resistance, junction to case	per diode	R_{thJC}	Mounting surface, flat, smooth and greased	-	-	1.1	°C/W
	(FULL-PAK) per diode			-	-	3.5	
Marking device			Case style TO-220AB	30CTH02			
			Case style TO-220 FULL-PAK	30CTH02FP			

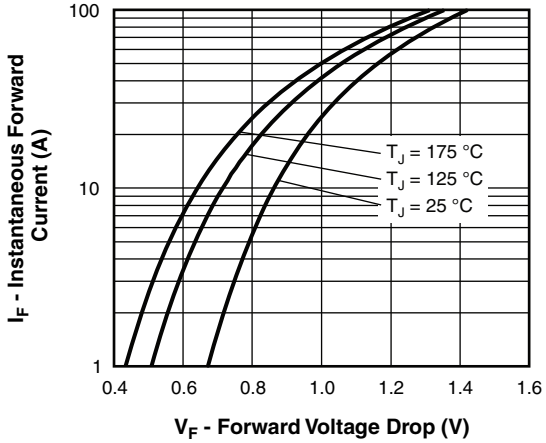


Fig. 1 - Typical Forward Voltage Drop Characteristics

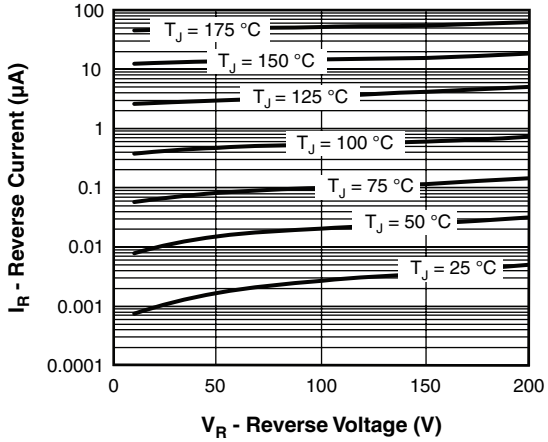


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

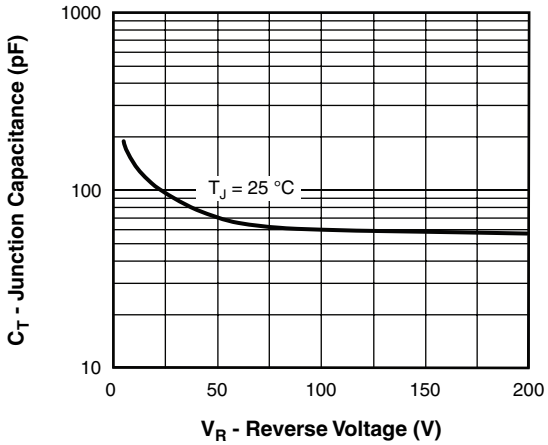


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

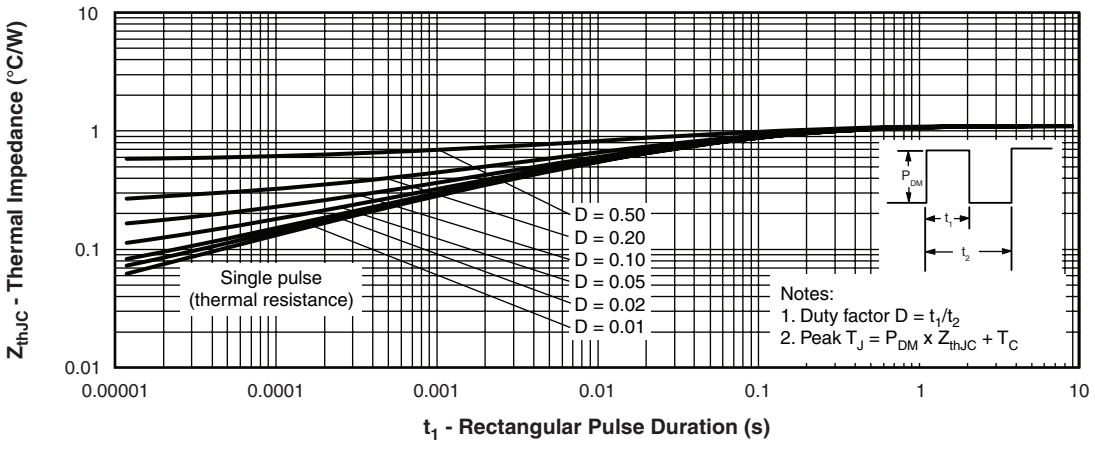


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

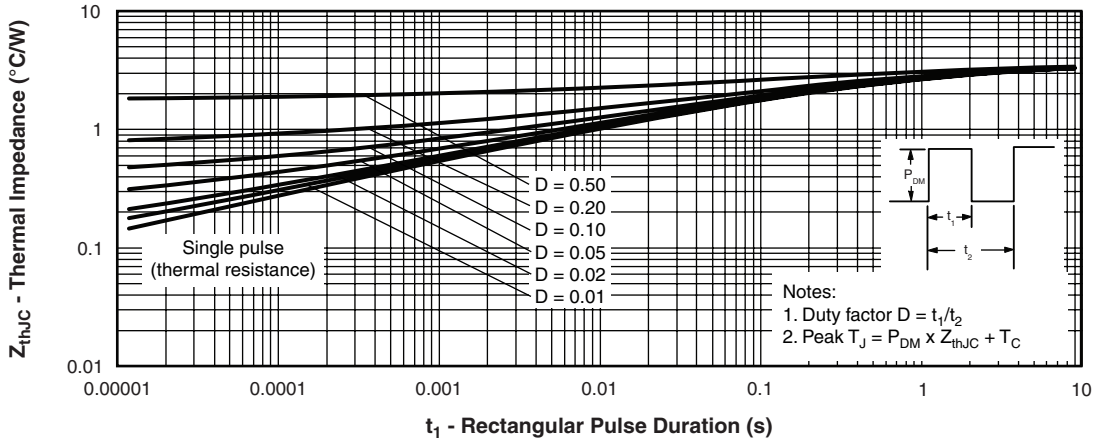


Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)

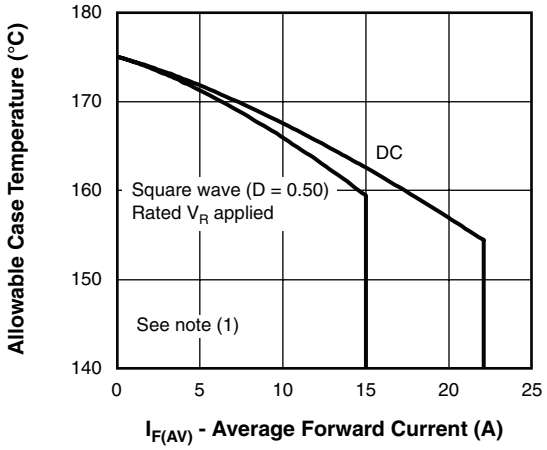


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

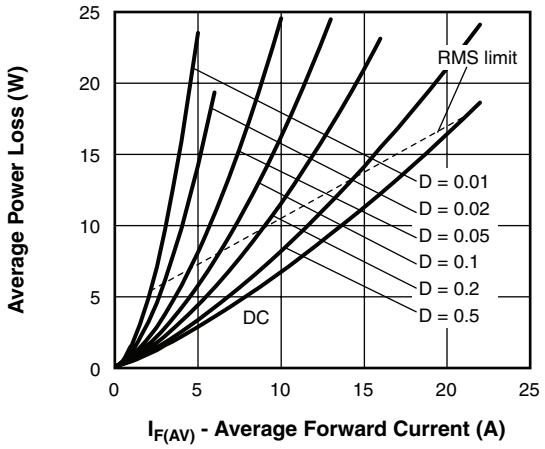


Fig. 8 - Forward Power Loss Characteristics

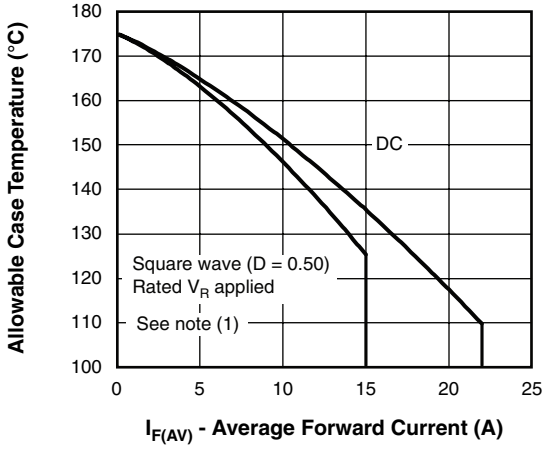


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

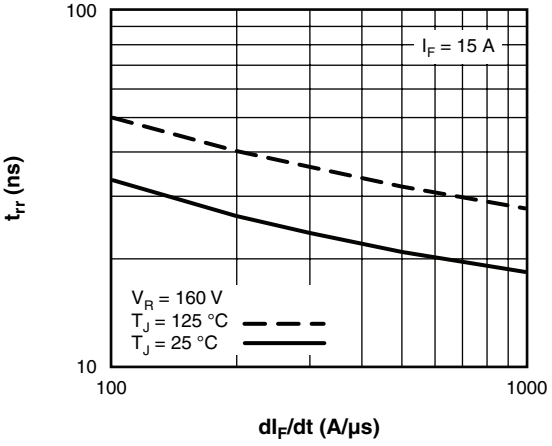


Fig. 9 - Typical Reverse Recovery Time vs. dI_F/dt

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;
Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}$/D) (see fig. 8);
Pd_{REV} = Inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = Rated V_R

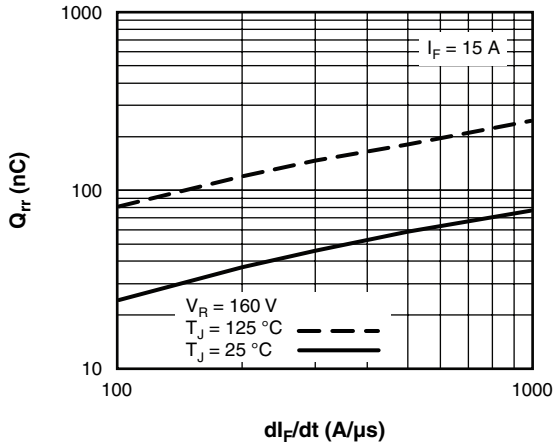


Fig. 10 - Typical Stored Charge vs. dI_F/dt

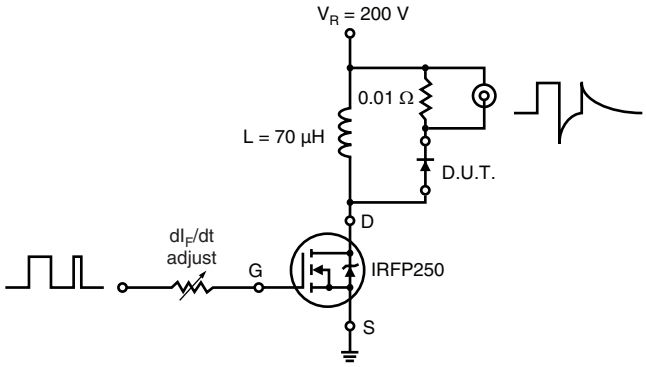
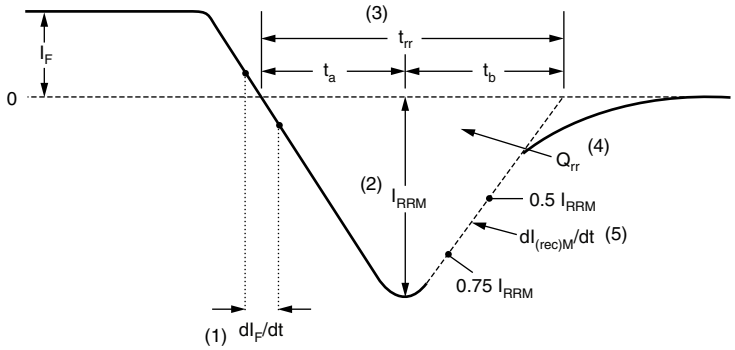


Fig. 11 - Reverse Recovery Parameter Test Circuit



(1) dI_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

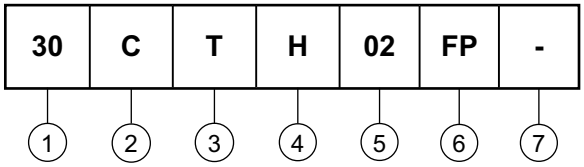
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 12 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



1 - Current rating (30 = 30 A)

2 - C = Common cathode

3 - T = TO-220, D^2PAK

4 - H = Hyperfast recovery

5 - Voltage rating (02 = 200 V)

6 - • None = TO-220AB
• FP = TO-220 FULL-PAK

7 - • None = Standard production
• PbF = Lead (Pb)-free

Tube standard pack quantity: 50 pieces

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95040
Part marking information	http://www.vishay.com/doc?95042

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